

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Shunpei YAMAZAKI et al. Art Unit : 2826
Serial No. : 09/773,543 Examiner : Victor A. Mandala, Jr.
Filed : February 2, 2001 Confirmation No.: 8040
Title : SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING THE
SAME

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

REPLY TO ACTION OF AUGUST 14, 2003

In reply to the Office Action of August 14, 2003, applicants submit the following remarks.

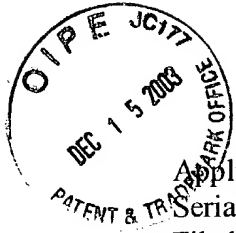
Claims 1-37 are pending in this application, with claims 1, 9, 21, 28, and 33 being independent.

Applicants acknowledge with appreciation the Examiner's allowance of claims 28-37 and the Examiner's indication that claims 2, 4, 7, 11, 13, 14, 17, 22, 23 and 26 are directed to allowable subject matter.

Claims 1, 3, 5, 6, 8-10, 12, 15, 16, 18-21, 24, 25 and 27 have been rejected as being anticipated by Yamazaki.

Independent claim 1 recites a semiconductor device that includes, among other elements, a second insulating film covering at least one electrode and a source wiring, and a gate wiring formed on the second insulating film and connected to the electrode. The action contends that second conductive layer 1716 of Figs. 17A and 17B of Yamazaki corresponds to the recited gate wiring and that third insulating film 1727 of Figs. 17A and 17B of Yamazaki corresponds to the recited second insulating film. However, as clearly shown in Fig. 17B, the second conductive layer 1716 is not formed on the third insulating film 1727. Accordingly, for at least this reason, applicants request reconsideration and withdrawal of the rejection of claim 1 and the claims the depend from it.

Independent claim 9 also recites a semiconductor device that includes, among other elements, a second insulating film covering at least one electrode and a source wiring, and a gate



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wiring formed on the second insulating film and connected to the at least one electrode. The action contends that second conductive layer 1718 of Figs. 17A and 17B of Yamazaki corresponds to the recited gate wiring and that third insulating film 1727 of Figs. 17A and 17B of Yamazaki corresponds to the recited second insulating film. However, as clearly shown in Fig. 17B, the second conductive layer 1718 is not formed on the third insulating film 1727. Accordingly, for at least this reason, applicants request reconsideration and withdrawal of the rejection of claim 9 and the claims the depend from it.

Independent claim 21 also recites a semiconductor device that includes, among other elements, a second insulating film covering at least one electrode and a source wiring, and a gate wiring formed on the second insulating film and connected to the at least one electrode. The action contends that second conductive layer 1716 of Figs. 17A and 17B of Yamazaki corresponds to the recited gate wiring and that third insulating film 1727 of Figs. 17A and 17B of Yamazaki corresponds to the recited second insulating film. As discussed above with respect to claim 1, Fig. 17B clearly shows that the second conductive layer 1716 is not formed on the third insulating film 1727. Accordingly, for at least this reason, applicants request reconsideration and withdrawal of the rejection of claim 21 and the claims the depend from it.

For the foregoing reasons, applicants submit that all claims are in condition for allowance.

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Attorney's Docket No.: 12732-012001 / US4638

Enclosed is a \$110 check for the Petition for Extension of Time fee. Please apply any other charges or credits to deposit account 06-1050.

Respectfully submitted,

Date: 12/15/03



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